SiPower

Power Semiconductor Technology

T4SB (20~80)F
Bridge Rectifier

■ Features

- I_o 4.0A
- V_{RRM} 200V~800V
- Glass passivated chip
- High surge forward current capability
- HF product

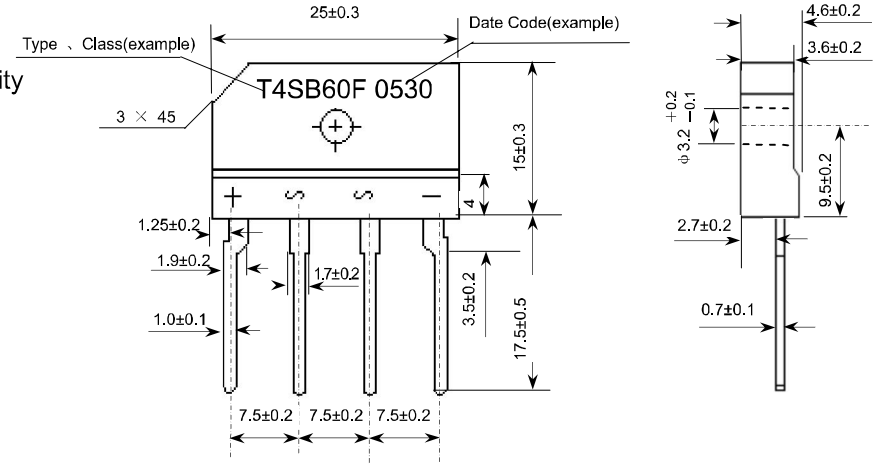
■ Applications

- General purpose 1 phase Bridge rectifier applications

Outline Dimensions and Mark

3S

Unit：mm



■ Limiting Values（Absolute Maximum Rating）

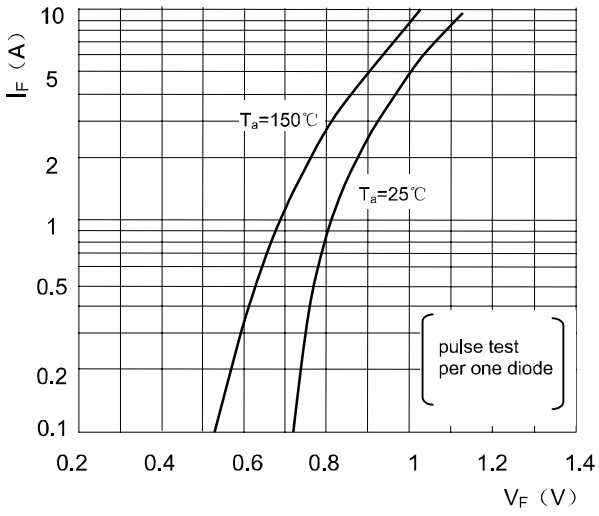
Item	Symbol	Unit	Conditions		T4SB 20 F	40 F	60 F	80 F
Storage Temperature	T_{stg}	℃			-40 ~ +150			
Junction Temperature	T_j	℃			+150			
Repetitive Peak Reverse Voltage	V_{RRM}	V			200	400	600	800
Average Rectified Output Current	I_o	A	50Hz sine wave, R-load,	With heatsink T_c=108℃	4.0			
				Without heatsink T_a=25℃	2.3			
Surge(Non-repetitive)Forward Current	I_{FSM}	A	50Hz sine wave, 1 cycle, T_a=25℃		150			
Current Squared Time	I^2t	A^2s	1ms≤t<8.3ms T_j=25℃,Rating of per diode		93			
Dielectric Strength	Vdis	kV	Terminals to case，AC 1 minute		2			
Mounting Torque	TOR	kg • cm	Recommend torque：5kg • cm		8			

■ Electrical Characteristics（T_a=25℃ Unless otherwise specified）

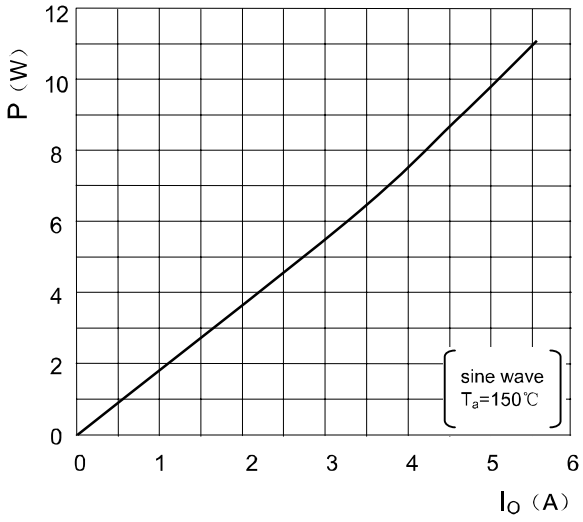
Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=2.0A, Pulse measurement, Rating of per diode	0.95
Peak Reverse Current	I_{RRM1}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J\text{-}A}$	℃/W	Between junction and ambient, Without heatsink	30
	$R_{\theta J\text{-}L}$		Between junction and lead, Without heatsink	6
	$R_{\theta J\text{-}C}$		Between junction and case, With heatsink	5.5

SiPower - The official marketing arm of Zhonghuan Semiconductor

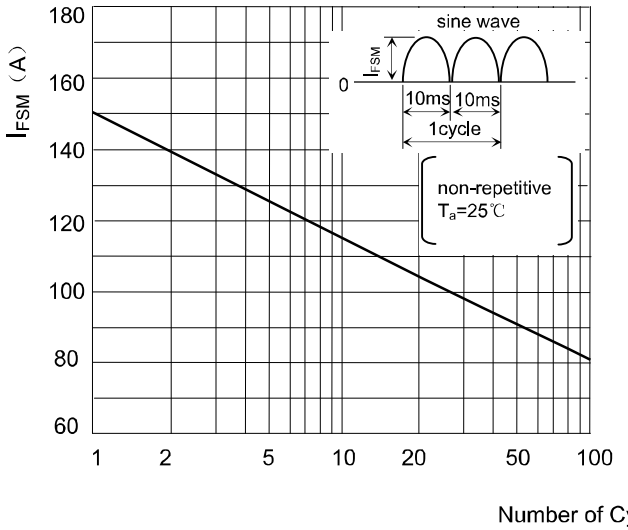
■ Characteristics(Typical)



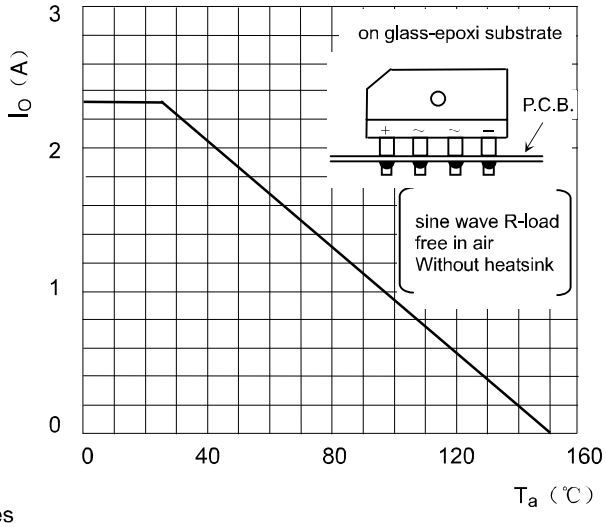
Forward Characteristics



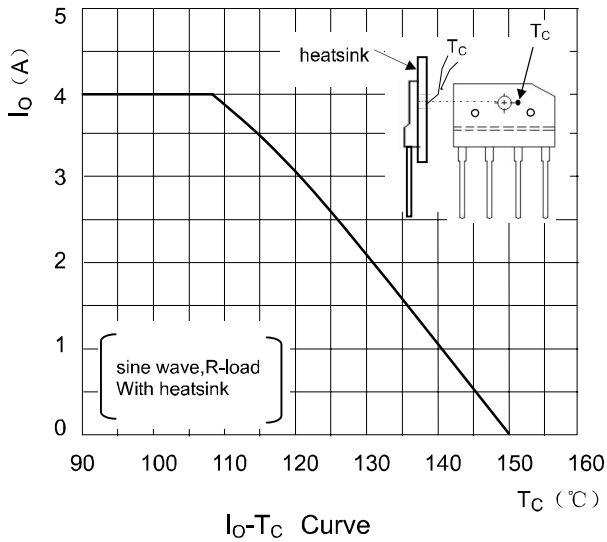
P-I_O Curve



Surge Forward Current Capability



I_O-T_a Curve



I_O-T_C Curve